

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

C. Amendments to the Claims.

1. (Currently Amended): A method, comprising:

- 5 cleaning a plasma reactor chamber part of a material redistributed
thereon by a reactive plasma process, by placing the chamber part in a
redistributed material solvent for at least 6 hours;
 cleaning the chamber part with a plasma that includes oxygen as a
 source gas; and
 ultrasonically cleaning the chamber part.

10 2. (Original) The method of claim 1, wherein:

 the material includes photoresist polymers and the solvent includes
acetone.

15 3. (Original) The method of claim 1, wherein:

 the chamber part comprises quartz.

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4. (Cancelled): The method of claim 1, wherein:

 the chamber part is placed in the solvent for at least 6 hours.

20 5. (Cancelled) The method of claim 1, further including:

 cleaning the chamber part with a plasma that includes oxygen as a source
gas.

6. (Currently Amended) The method of claim 1, wherein:

25 the plasma is formed with a radio frequency (RF) power in the general
range of 500 to 1000 W.

7. (Currently Amended) The method of claim 1, further including:

30 rinsing the chamber part after cleaning with the solvent but before the
plasma cleaning.

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8. (Cancelled) The method of claim 5, further including:
ultrasonically cleaning the chamber part.

5 9. (Currently Amended) The method of claim 1 5, further including:
baking the chamber part at a temperature in the general range of 75-150
°C.

10 10. (Previously Amended) A method of cleaning a plasma reactor chamber part, comprising:
plasma cleaning a chamber part of a material redistributed on the
chamber part by a reactive plasma process, with a plasma having an etch
selectivity between the chamber part and the redistributed material that is
greater than 1:100; and
cleaning the chamber part with a solvent of the redistributed material
by placing the chamber part in the solvent of the redistributed material.

11. (Original) The method of claim 10, wherein:
the chamber part comprises quartz and the plasma includes oxygen as
a source gas.

20 12. (Original) The method of claim 10, wherein:
the plasma is formed with a radio frequency (RF) power in the general
range of 500 to 1000 W.

25 13. (Original) The method of claim 10, wherein:
the redistributed material includes photoresist polymers.

14. (Cancelled) The method of claim 10, further including:
cleaning the chamber part with a solvent of the redistributed material.

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15. (Previously Amended) A method of cleaning reactive plasma chamber parts, comprising the steps of:

applying an organic solvent to a surface of a chamber part;
oxygen plasma cleaning the chamber part; and
ultrasonically cleaning the chamber part after the oxygen plasma
cleaning.

5 16. (Original) The method of claim 15, wherein:
the organic solvent includes acetone.

10 17. (Reinstated) The method of claim 15, further including:
rinsing the chamber part with de-ionized water after applying the
organic solvent.

18. (Cancelled) The method of claim 15, further including:
ultrasonically cleaning the chamber part after the oxygen plasma cleaning.

15 19. (Currently Amended) The method of claim ~~18~~ 15, further including:
rinsing the chamber part with a liquid that evaporates at a lower
temperature than water after the ultrasonic cleaning.

20 20. (Original) The method of claim 15, further including:
baking the chamber part at a temperature greater than 80 °C for at least 15
minutes.